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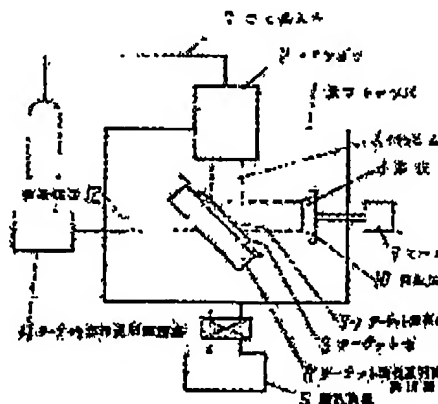
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**(54) ION BEAM SPUTTERING DEVICE**

**(57)Abstract:**

**PURPOSE:** To easily control the composition of a thin film composed of plural components and formed on a substrate by moving a target part in which plural kinds of targets are mosaically arranged and making the area ratio among respective targets in an ionic irradiation region variable.

**CONSTITUTION:** In a vacuum chamber 1, a target part 3 in which plural kinds of targets are mosaically arranged is irradiated by an ion beam 6 formed by ionizing an inert gas by means of an ion gun 2, by which the targets are sputtered and a thin film of plural components is formed on a substrate 4 held by a rotary plate 10. In the above ion beam sputtering device, the above target part 3 is moved by means of a target part position control circuit 11 via a target part position control mechanism section 8, by which the area ratio among respective targets in the ion beam irradiation region in the target part 3 can be regulated. By this method, the above thin film can be formed into the desired composition.



**LEGAL STATUS**

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